

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Group Art Unit: Not yet assigned

Examiner: Not yet assigned

Serial No. Not yet assigned

Filed: December 28, 2001

In re Application of: Hawley et al.

For: METHOD FOR FABRICATING A MOS TRANSISTOR HAVING IMPROVED
TOTAL RADIATION-INDUCED LEAKAGE CURRENT

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I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as Express Mailing Label No. EL858979185US, in an envelope addressed to Director of Patents, Box New Application, Washington, D.C. 20231 on 12/28/01, Signed Stephanie Davis

PRELIMINARY AMENDMENT

Director of Patents
Box New Application
Washington, D.C. 20231

Dear Sir:

Kindly amend the above-identified application as follows.

In the Specification:

Page 1, Line 8, please delete "MOS TRANSISTOR HAVING IMPROVED TOTAL RADIATION-INDUCED LEAKAGE CURRENT AND METHOD FOR FABRICATING SAME" and insert --METHOD FOR FABRICATING A MOS TRANSISTOR HAVING IMPROVED TOTAL RADIATION-INDUCED LEAKAGE CURRENT--.

Page 1, Line 11, please insert -This application is a divisional of United States Patent Application Serial Number 09/741,949, filed December 20, 2000, entitled "MOS TRANSISTOR HAVING IMPROVED TOTAL RADIATION-INDUCED LEAKAGE CURRENT AND METHOD FOR FABRICATING SAME".-